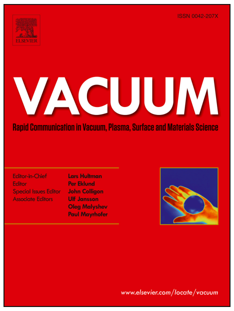

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PII: S0042-207X(17)31360-X
DOI: 10.1016/j.vacuum.2018.01.007
Reference: VAC 7756

To appear in: *Vacuum*

Received Date: 29 September 2017
Revised Date: 19 December 2017
Accepted Date: 4 January 2018

Please cite this article as: Ramadam R, Gabriel Simiz J, Ynsa MaríDolores, Manso Silván M, Microwave plasma annealing of sol-gel deposited tantalum oxide and zinc oxide films, *Vacuum* (2018), doi: 10.1016/j.vacuum.2018.01.007.

Microwave plasma annealing of sol-gel deposited tantalum oxide and zinc oxide films

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